NON-VOLATILE MEMORY MANUFACTURING METHOD USING STI TRENCH IMPLANTATION

ABSTRACT

A method for manufacturing an integrated circuit structure includes providing a semiconductor substrate and forming two trenches in the semiconductor substrate to define an active region therebetween. An implanted source region is formed in one of the trenches on one side of the active region. An implanted drain region is formed in the other trench on the other side of the active region. Shallow trench isolations are then formed in the trenches. One or more gates are formed over the active region, and contacts to the implanted source region and the implanted drain region are formed.

Figure 5A